

# Notice of Allowability

Application No.

10/814,867

Examiner

My-Trang N. Ton

Applicant(s)

BERNARD ET AL.

Art Unit

2816

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address--

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1. ☒ This communication is responsive to Amdt. filed 6/9/06.
2. ☒ The allowed claim(s) is/are 1-91 and 93-100.
3. ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
  - a) ☐ All b) ☐ Some\* c) ☐ None of the:
    1. ☐ Certified copies of the priority documents have been received.
    2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
    3. ☐ Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

\* Certified copies not received: \_\_\_\_\_.

Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.

**THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.**

4. ☐ A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.
  5. ☐ CORRECTED DRAWINGS (as "replacement sheets") must be submitted.
    - (a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached
      - 1) ☐ hereto or 2) ☐ to Paper No./Mail Date \_\_\_\_\_.
    - (b) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date \_\_\_\_\_.
- Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).
6. ☐ DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

## Attachment(s)

1. ☐ Notice of References Cited (PTO-892)
2. ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
3. ☒ Information Disclosure Statements (PTO-1449 or PTO/SB/08), Paper No./Mail Date 6/9/06
4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material
5. ☐ Notice of Informal Patent Application (PTO-152)
6. ☐ Interview Summary (PTO-413), Paper No./Mail Date \_\_\_\_\_
7. ☐ Examiner's Amendment/Comment
8. ☒ Examiner's Statement of Reasons for Allowance
9. ☐ Other \_\_\_\_\_

  
**MY-TRANG N. TON**  
**PRIMARY EXAMINER**

### **Reasons for allowance**

The following is an examiner's statement of reasons for allowance:

1. As noted in the previous Office action, none of the prior art disclosed or suggested to show the particular structure and/or the particular operation recited in these claims namely: "a diode" in combination with "a first pFET", "a second pFET" and "a high-voltage MOS nFET" as recited in claims 1 and 62; "a diode" in combination with "a first pFET", "a second pFET", "a high-voltage MOS nFET", "a pull-up circuit" and "a capacitor" as recited in claim 8; "a diode" and "a high-voltage MOS nFET" in combination with "a first pFET", "a second pFET" and "a MOS nFET" as recited in claim 13; "a diode" and "a high-voltage MOS nFET" in combination with "a first pFET", "a second pFET", "a MOS nFET" and "a pull-up circuit" as recited in claim 22; "a diode" (or a first diode) in combination with "a first pFET", "a second pFET", "third pFET" and "a high-voltage MOS nFET" as recited in claims 31, 36 and 54; set-reset latch circuit" and "a first diode" in combination with "a first pFET", "a second pFET" and "a high-voltage MOS nFET" as recited in claim 41; "a first high-voltage nFET" and "a diode" in combination with "a first pFET", "a second pFET" and "a second high-voltage nFET" as recited in claim 68; "a first and a second high-voltage nFET" and "a first and second diodes" in combination with "a first and a second pFET" and "a third and a fourth pFET" as recited in claim 74; the combination of "a first and a second pFET", "a first circuit portion", "a second circuit portion", "a third and fourth pFET" and "a first and a second high-voltage circuit portion" as recited in claim 77; "first – second diodes" in combination with "first - fourth pFETs" and "a first and a second high-voltage circuit

portion" as recited in claim 90; "a first and a second n-well diode", "a third and fourth pFET" and "a first and a second high-voltage circuit portion" in combination with "a first and a second pFET" as recited in claim 96.

2. The prior art references submitted by the applicant on IDS form received on 6/9/06 was reviewed and considered. However, these references still lack the combination limitations as cited in the claims. Therefore, the claims are patentably distinct over all these prior art references of record.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to My-Trang N. Ton whose telephone number is 571-272-1754. The examiner can normally be reached on 7:00 a.m - 5:30 p.m.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Timothy Callahan can be reached on 571-272-1740. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.



My-Trang N. Ton  
Primary Examiner  
Art Unit 2816

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